

Schottky Diodes

1N5817W ~ 1N5819W

■ Features

- Low power loss, high efficiency
- High current capability
- Low forward voltage drop
- High Surge Capability

SOD-123



Top View



PIN DESCRIPTION

PIN	DESCRIPTION
1	Cathode
2	Anode

■ Absolute Maximum Ratings $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	1N5817W	1N5818W	1N5819W	Unit
Peak Repetitive Reverse Voltage	VRRM	20	30	40	V
RMS Voltage	VRMS	14	21	28	
DC Blocking Voltage	VDC	20	30	40	
Forward Voltage @ IF=1A	VF	0.45	0.55	0.6	
Forward Voltage @ IF=3.1A		0.75	0.875	0.9	
Average Forward Rectified Current @ TL=90℃	IFAV	1			A
Non-Repetitive Peak Forward Surge Current @8.3ms	IFSM	25			
Reverse Voltage Leakage Current Ta = 25℃ Ta = 100℃	IR	1			mA
		10			
Typical Junction Capacitance	CJ	110			pF
Junction Temperature	TJ	125			℃
Storage Temperature range	Tstg	-55 to 125			

■ Marking

NO.	1N5817W	1N5818W	1N5819W
Marking	12A	13A	14A

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■ Typical Characteristics

Fig.1 Forward Current Derating Curve

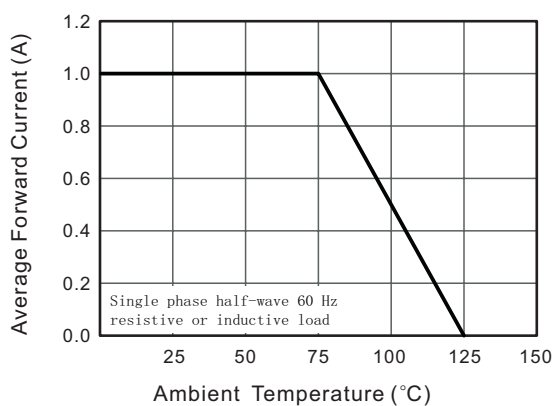


Fig.2 Typical Reverse Characteristics

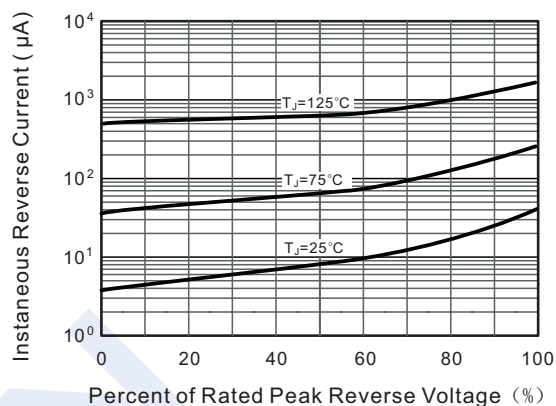


Fig.3 Typical Forward Characteristic

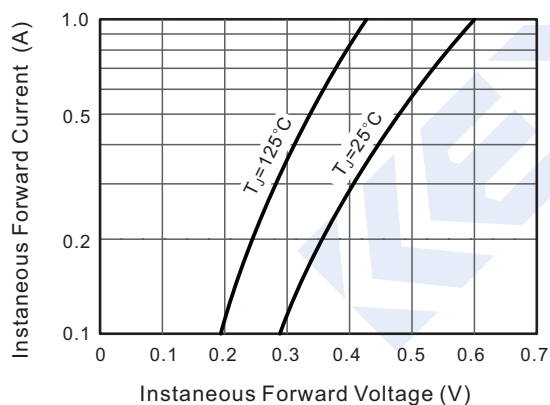


Fig.4 Typical Junction Capacitance

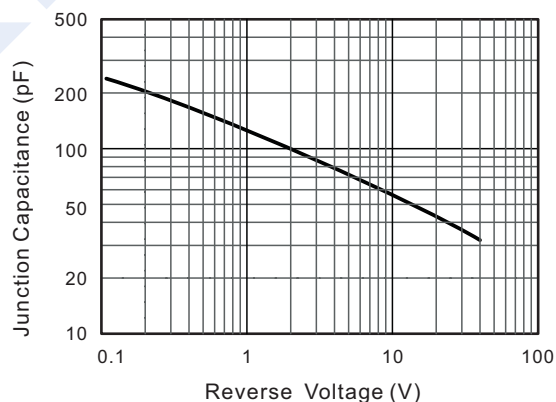


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

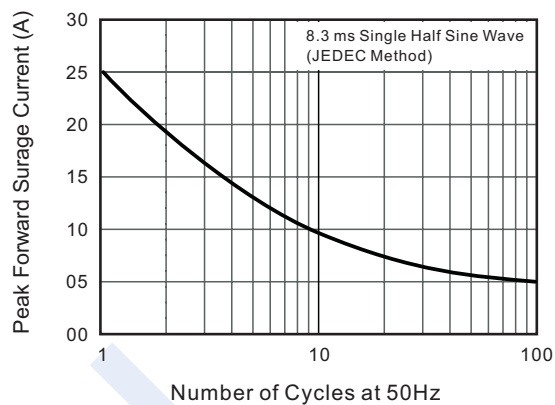
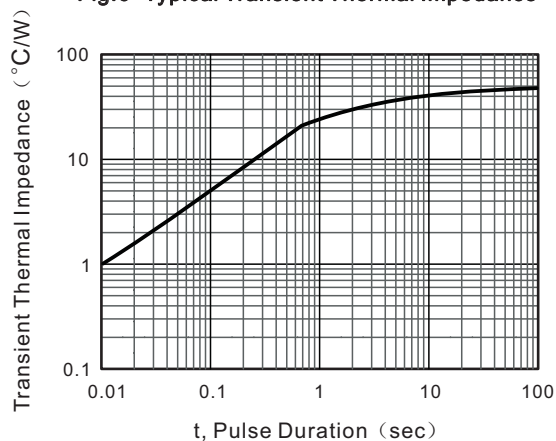


Fig.6- Typical Transient Thermal Impedance



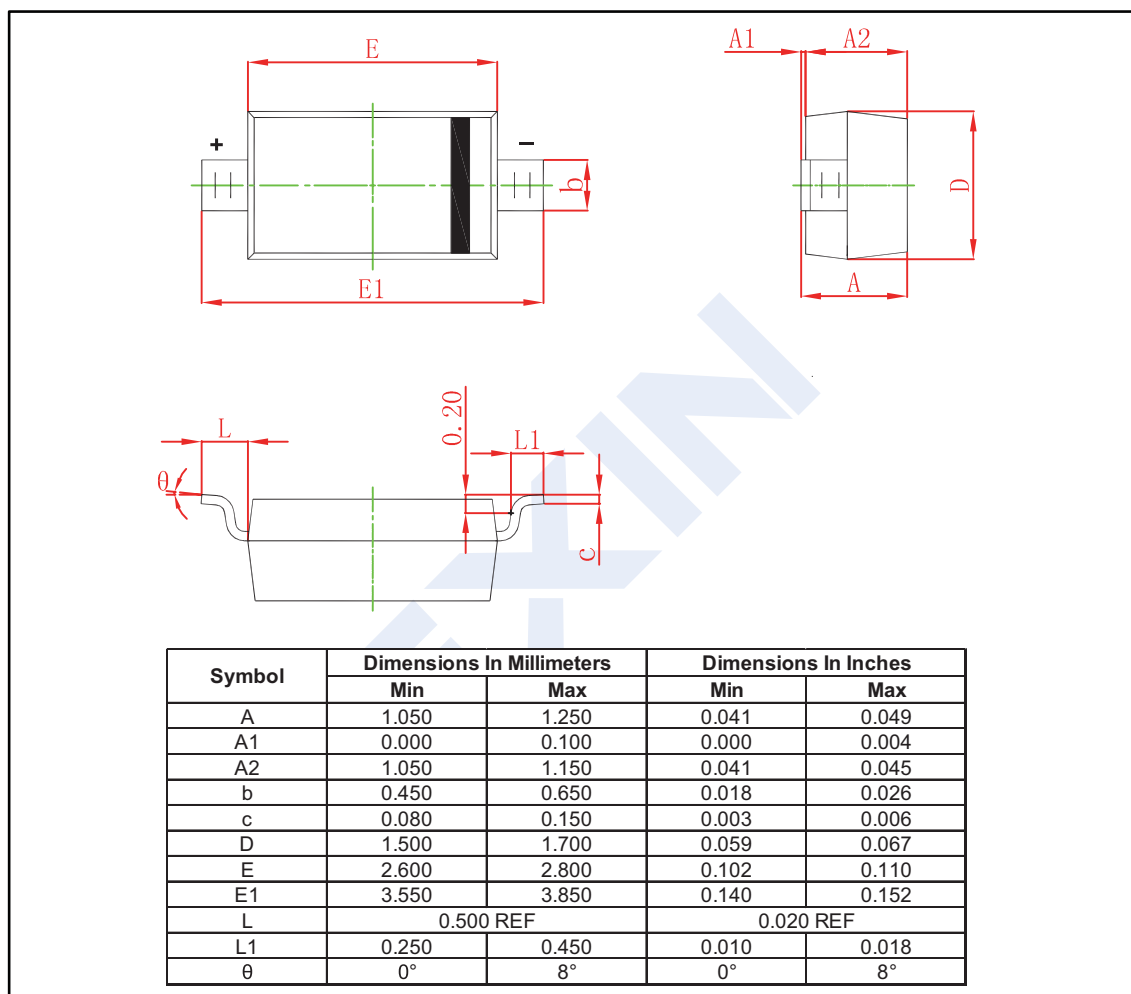
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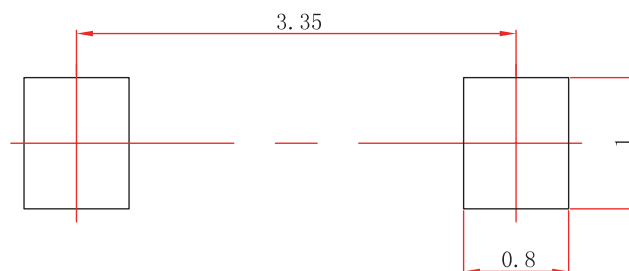
■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-123



■ The Recommended Mounting Pad Size



Note:

1. Controlling dimension in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.